

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE025N30G uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

**100% UIS TESTED!**

**100%  $\Delta V_{ds}$  TESTED!**

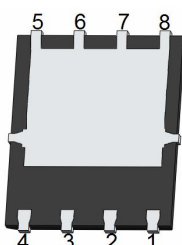
### General Features

- $V_{DS} = 30V, I_D = 115A$   
 $R_{DS(ON)} = 2.2m\Omega$  (typical) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 3.6m\Omega$  (typical) @  $V_{GS} = 4.5V$
- High density cell design for ultra low  $R_{dson}$
- Very low on-resistance  $R_{DS(on)}$
- Good stability and uniformity with high  $E_{AS}$
- 150 °C operating temperature
- Pb-free lead plating

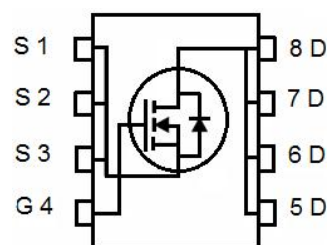
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
025N30G	NCE025N30G	DFN 5x6-8L	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	115	A
Drain Current-Continuous( $T_C = 100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	81	A
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	460	A
Maximum Power Dissipation	$P_D$	70	W
Derating factor		0.56	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	384	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ\text{C}$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.79	$^\circ\text{C/W}$
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## Electrical Characteristics (TC=25°C unless otherwise noted)

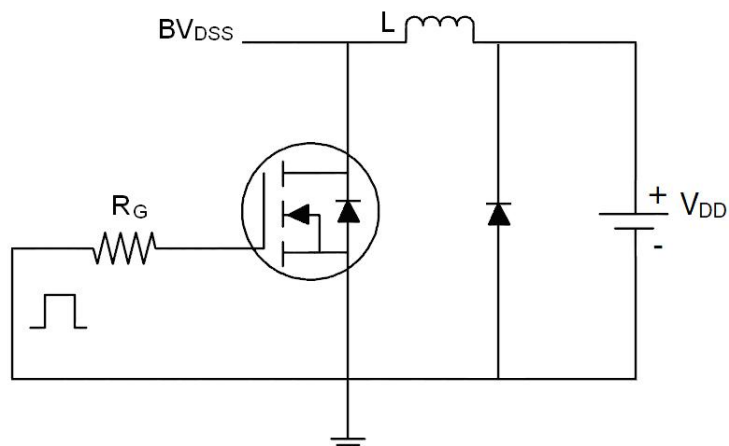
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	2.2	2.9	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	3.6	5.2	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	3120	-	PF
Output Capacitance	C <sub>oss</sub>		-	445	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	421	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>GEN</sub> =6Ω	-	11	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	16	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	7	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	71	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	10.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	16.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	115	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs (Note3)	-	30	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	60	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

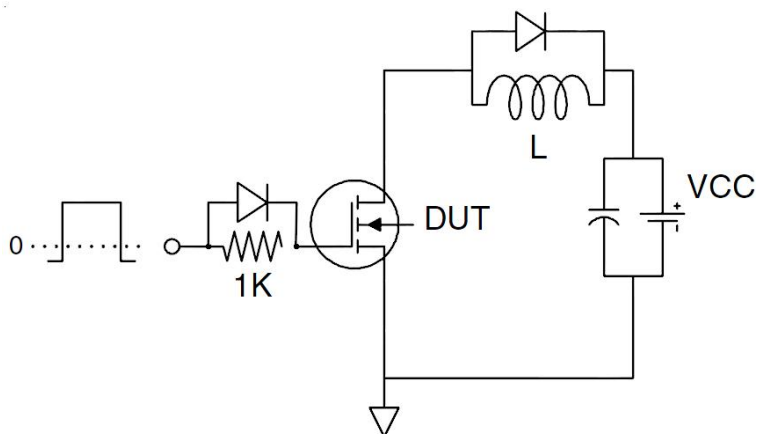
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$

## Test Circuit

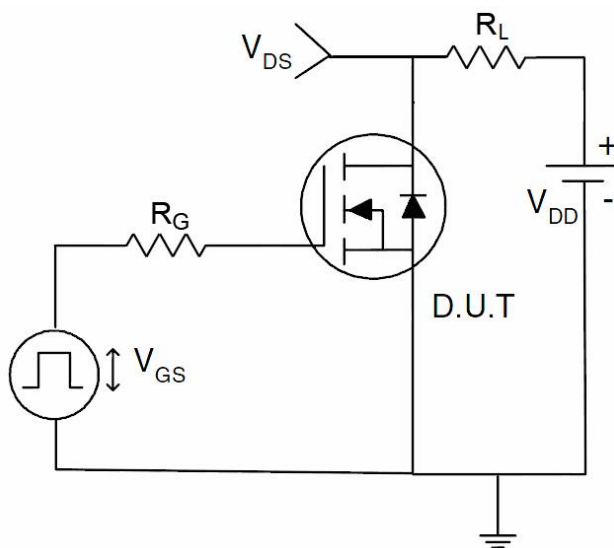
### 1) $E_{AS}$ Test Circuits



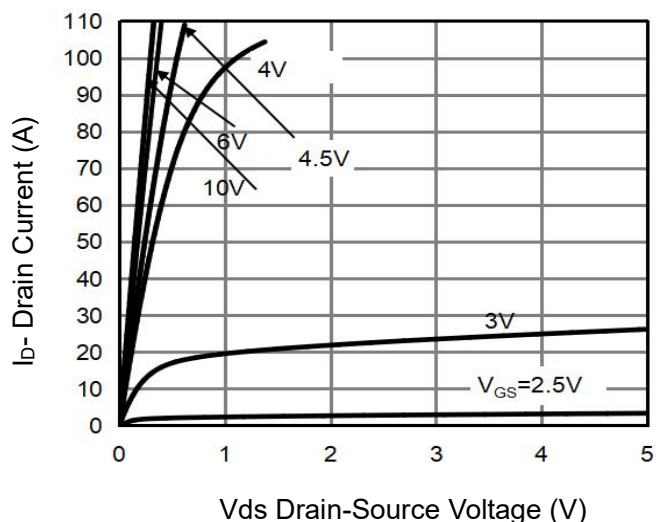
### 2) Gate Charge Test Circuit



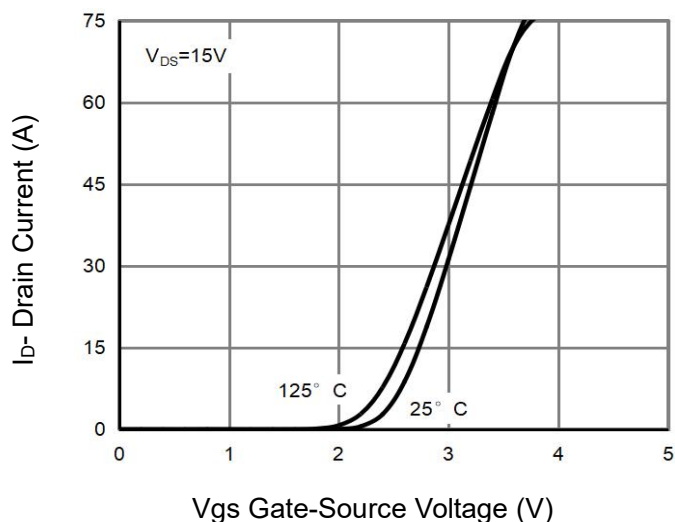
### 3) Switch Time Test Circuit



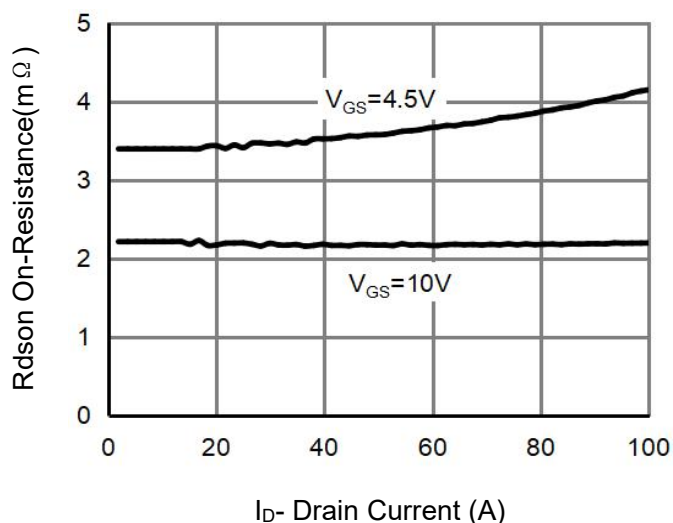
## Typical Electrical and Thermal Characteristics (Curves)



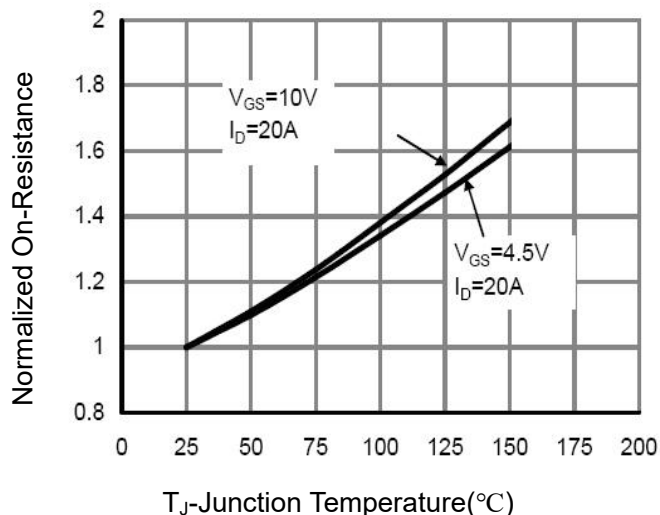
**Figure 1 Output Characteristics**



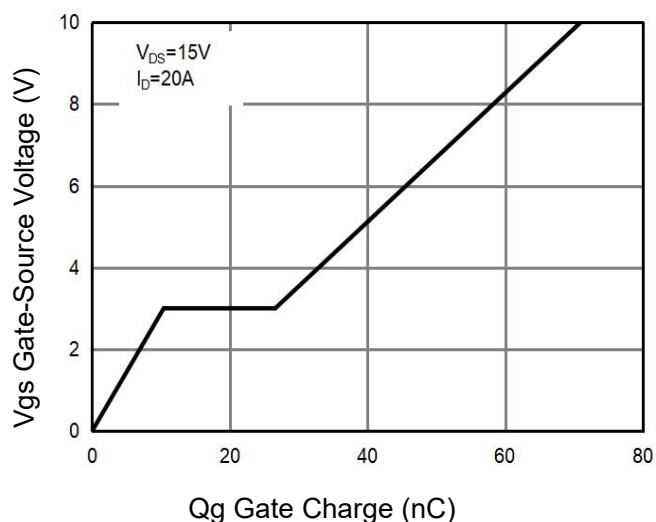
**Figure 2 Transfer Characteristics**



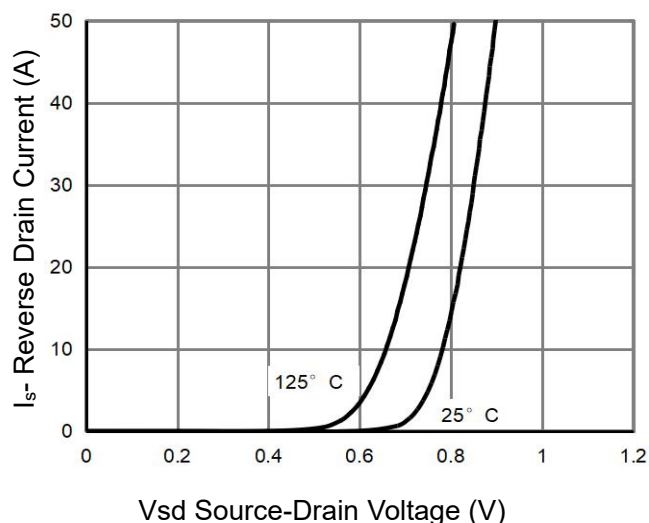
**Figure 3  $R_{DS(on)}$ - Drain Current**



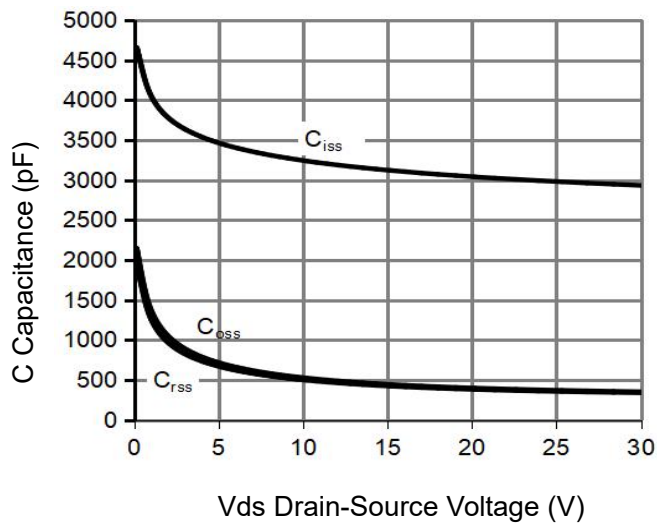
**Figure 4  $R_{DS(on)}$ -Junction Temperature**



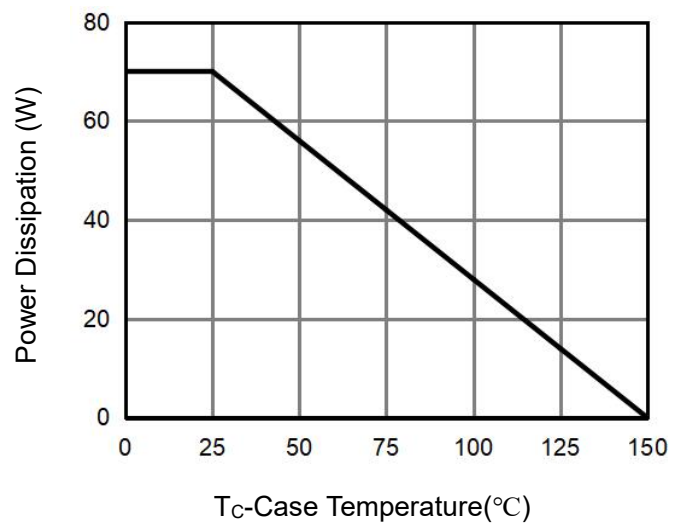
**Figure 5 Gate Charge**



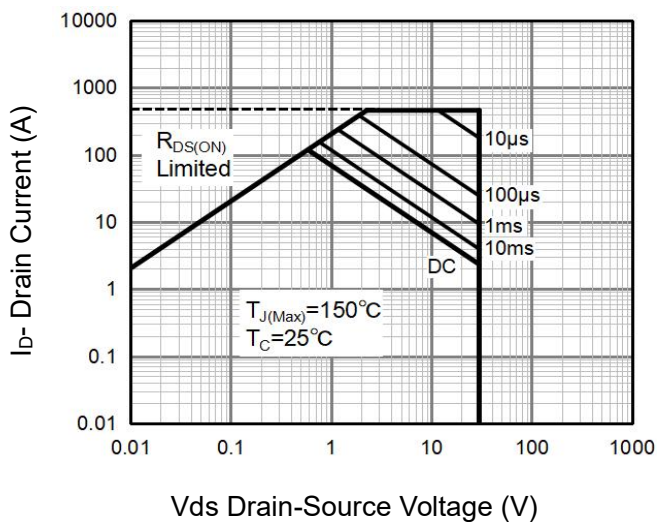
**Figure 6 Source- Drain Diode Forward**



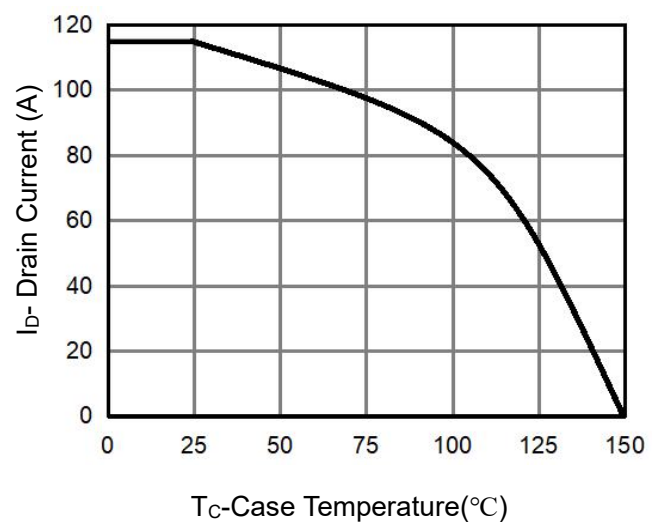
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



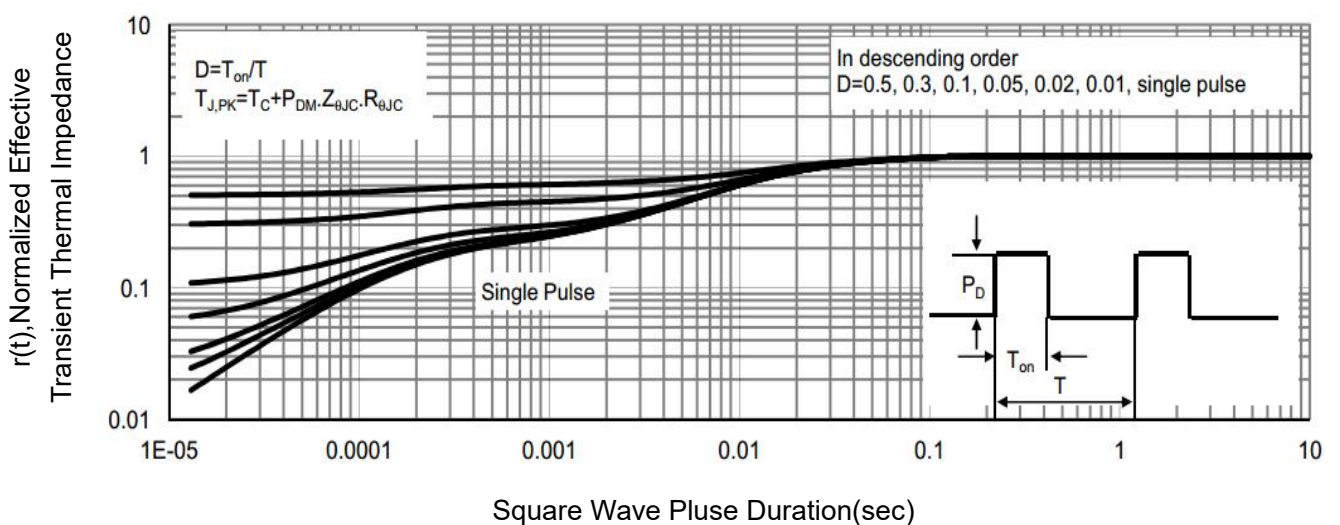
Tc-Case Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**

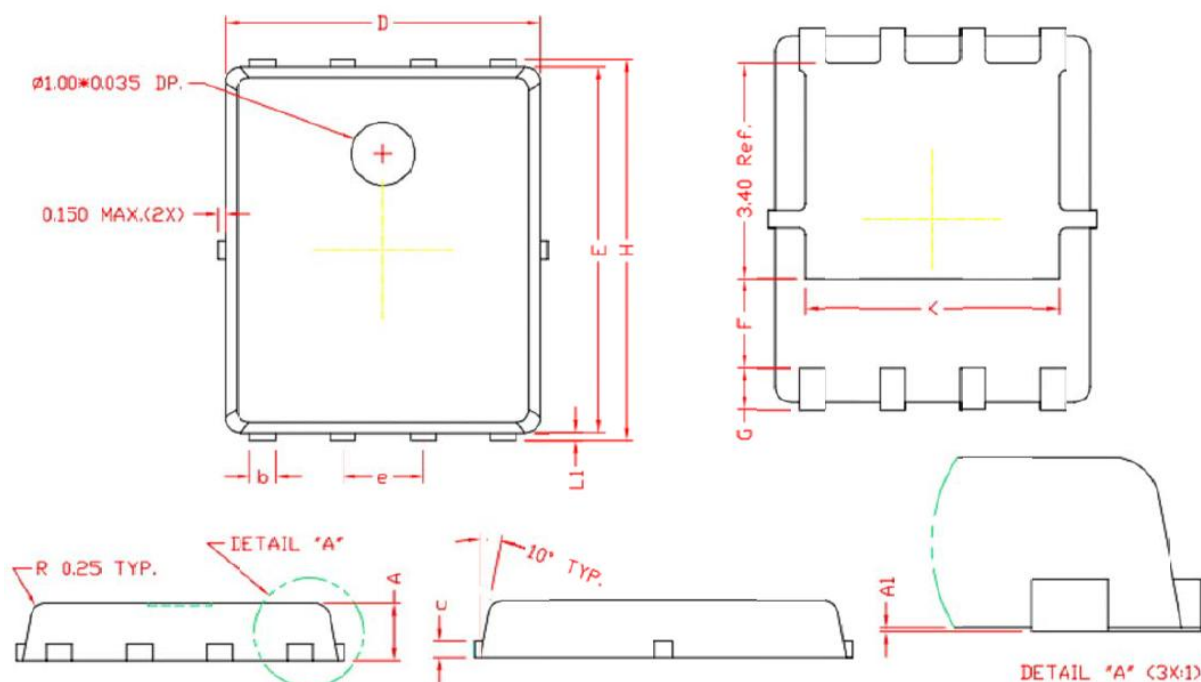


Tc-Case Temperature(°C)  
**Figure 10 ID Current- Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L Package Information



### COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
b	0.35	0.42	0.49
c	0.254 REF.		
D	4.90	5.00	5.10
F	1.40 REF.		
E	5.70	5.80	5.90
e	1.27 BSC.		
H	5.95	6.08	6.20
L1	0.10	0.14	0.18
G	0.60 REF.		
K	4.00 REF.		



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